

ABSTRACT

A method of making a monitoring pattern to measure a depth and profile of a shallow trench isolation is disclosed. An example method of making a monitoring pattern of a shallow trench isolation profile forms a first pattern on a substrate to monitor a depth of a first shallow trench isolation. In the example method, the first pattern includes a plurality of unequally spaced active regions on the substrate. The example method also forms a second pattern on the substrate to measure electrical effects associated with a depth and a profile of a second shallow trench isolation. In the example method, the second pattern includes a plurality of equally spaced active regions on the substrate and a plurality of contact regions that electrically connect the equally spaced active regions.